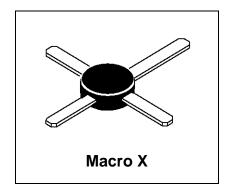


\*G Denotes RoHS Compliant, Pb free Terminal Finish

# RF & MICROWAVE DISCRETE LOW POWER TRANSISTORS

#### **Features**

- Low Noise 2.5 dB @ 500 MHZ
- Gain at Optimum Noise Figure = 15.5 dB @ 500 MHz
- Ftau 5.0 GHz @ 10v, 75mA
- Cost Effective MacroX Package



**DESCRIPTION:** Designed for high current, low power, low noise, amplifiers up to 1.0 GHz.

# **ABSOLUTE MAXIMUM RATINGS** (Tcase = 25°C)

Symbol	Parameter	MRF581	MRF581A	Unit
$V_{CEO}$	Collector-Emitter Voltage	18	15	Vdc
$V_{CBO}$	Collector-Base Voltage	3	30	Vdc
V <sub>EBO</sub>	Emitter-Base Voltage	2	.5	Vdc
I <sub>C</sub>	Collector Current	20		mA

#### **Thermal Data**

PD	Total Device Dissipation @ TC = 50°C Derate above 50°C	2.5 25	Watts mW/ <b>°C</b>
P <sub>D</sub>	Total Device Dissipation @ TC = 25°C Derate above 25°C	1.25 10	Watts mW/ <b>°C</b>
Tstg	Storage Junction Temperature Range	-65 to +150	°C
T <sub>Jmax</sub>	Maximum Junction Temperature	150	°C

#### **Revision A- December 2008**



**MRF581 MRF581G MRF581A** MRF581AG

# **ELECTRICAL SPECIFICATIONS (Tcase = 25°C)**

#### **STATIC**

(off)

0	Tank Oan ditions			1114		
Symbol	Test Conditions		Min.	Тур.	Max.	Unit
BVCEO	Collector-Emitter Breakdown Voltage (IC = 5.0 mAdc, IB = 0)	MRF581 MRF581A	18 15	-	-	Vdc
BVCBO	Collector-Base Breakdown Voltage (IC = 1.0 mAdc, IE = 0)		30	-	-	Vdc
BVEBO	Emitter-Base Breakdown Voltage (IE = 0.1 mAdc, IC = 0)		2.5	-	-	Vdc
ICBO	Collector Cutoff Current (VCB = 15 Vdc, VBE = 0 Vdc)		-	-	0.1	mA
IEBO	Emitter Cutoff Current (Vbe = 2.5 Vdc)		-	-	0.1	mA
(on)						
HFE	DC Current Gain (IC = 50 mAdc, VCE = 5.0 Vdc)	MRF581 MRF581A	50 90	-	200 250	-

### **DYNAMIC**

Symbol	Took Conditions		Value		l lmit
Symbol	Test Conditions	Min.	Тур.	Max.	Unit
СОВ	Output Capacitance (VCB = 10 Vdc, IE = 0, f = 1.0 MHz)	-	2.0	3.0	pF
Ftau	Current-Gain Bandwidth Product (IC = 75 mAdc, VCE = 10 Vdc, f = 1.0 GHz)	-	5.0	-	GHz



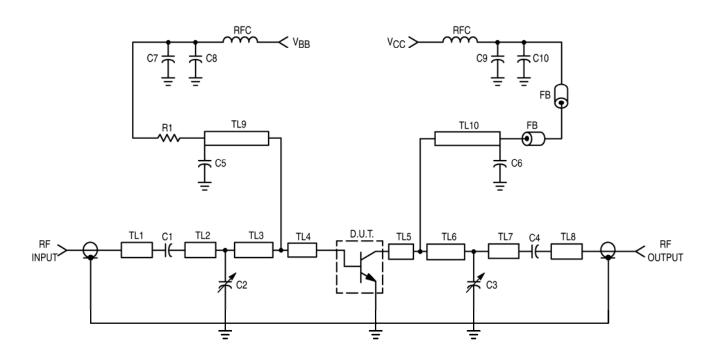
#### **FUNCTIONAL**

Cumb al	Took Conditions			l locit	
Symbol	Test Conditions	Min.	Unit		
NF	Noise Figure (50ohms) (IC = 50 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	-	3.0	3.5	dB
G NF	Power Gain @ NFmin (IC = 50 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	13	15.5		dB
G U max	Maximum Unilateral Gain (1) IC = 50 mAdc, VCE = 10 Vdc, f = 500 MHz	-	17.8	•	dB
MSG	Maximum Stable Gain IC = 50 mAdc, VCE = 10 Vdc, f = 500 MHz	-	20	-	dB
S <sub>21</sub>   <sup>2</sup>	Insertion Gain IC = 50 mAdc, VCE = 10 Vdc, f = 500 MHz	14	15	-	dB

Table 1. Common Emitter S-Parameters, @ VCE = 10 V, IC = 50 mA

f	S1	1		S21		S12		22
(MHz)	S11	∠ ф	S21	∠ ф	S12	∠ ф	S22	∠ ф
100	.610	-137	23.8	116	.026	46	.522	-78
200	.659	-161	13.2	98	.033	47	.351	-106
300	.671	-171	9.0	89	.040	51	.304	-120
400	.675	-178	6.8	83	.047	55	.292	-128
500	.677	176	5.5	77	.055	58	.293	-132
600	.678	172	4.6	72	.064	61	.299	-134
700	.677	168	4.0	68	.073	62	.306	-135
800	.679	184	3.5	64	.082	63	.314	-136
900	.678	160	3.1	60	.092	64	.322	-138
1000	.682	156	2.8	56	.102	65	.311	-139





C1, C4, C5, C6, C8, C9 — 1000 pF, Chip Capacitor C7, C10 — 10  $\mu$ F, Tantalum Capacitor RFC — VK–200, Ferroxcube TL1, TL7, TL8 — Microstrip 0.162, x 0.600, TL3 — Microstrip 0.162, x 0.800, TL5 — Microstrip 0.120, x 0.440, TL9, TL10 — Microstrip 0.025, x 4.250, Board Material — 0.0625, Thick Glass Teflon  $\epsilon$  r = 2.55

C2, C3 — 1.0–10 pF, Johanson Capacitor R1 — 1.0 k $\Omega$  Res.

FB — Ferrite Bead, Ferroxcube, 56-590-65/3B

TL2 — Microstrip 0.162, x 1.000, TL4 — Microstrip 0.162, x 0.440,

TL6 — Microstrip 0.120, x 1.160,

Figure 1. Minimum Noise Figure and Gain @ Minimum Noise Figure.



# RF Low Power PA, LNA, and General Purpose Discrete Selector Guide

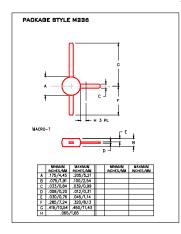
Раскапе	Device	Type	GPE Freq (MHz	Pout (watts)	GPE (dB)	Efficiency (%)	GPE VCC	BVCEO	IC max (mA)
SO-8	MRF4427, R2	NPN	175	0.15	18	60	12	20	400
TO-39	2N4427	NPN	175	1	10	50	12	20	400
POWER MACRO	MRF553	NPN	175	1.5	11.5	60	12.5	16	500
POWER MACRO	MRF553T	NPN	175	1.5	11.5	50	12.5	16	500
TO-39	MRF607	NPN	175	1.75	11.5	50	12.5	16	330
TO-39	2N6255	NPN	175	3	7.8	50	12.5	18	1000
TO-72	2N5179	NPN	200		20		6	12	50
MACRO X	MRF559	NPN	512	0.5	10	65	7.5	16	150
MA CRO X	MRF559	NPN	512	0.5	13	60	12.5	16	150
TO-39	2N3866A	NPN	400	1	10	45	28	30	400
SO-8	MRF3866, R1, R2	NPN	400	1	10	45	28	30	400
POWER MACRO	MRF555	NPN	470	1.5	11	50	12.5	16	400
POWER MACRO	MRF555T	NPN	470	1.5	11	50	12.5	16	400
MA CRO X	MRF559	NPN	870	0.5	6.5	70	7.5	16	150
MA CRO X	MRF559	NPN	870	0.5	9.5	65	12.5	16	150
SO-8	MRF8372,R1,R2	NPN	870	0.75	8	55	12.5	16	200
POWER MACRO	MRF557	NPN	870	1.5	8	55	12.5	16	400
POWER MACRO	MRF557T	NPN	870	1.5	8	55	12.5	16	400

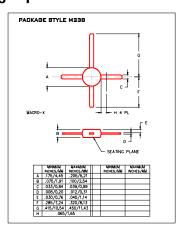
Packag	Device	Type	Freq (MHz)	NF (dB)	NF IC (mA)	NF VCE	GN (dB)	Gu Max (dB)	Ftau (MHz)	Ccb(pF)	BVCEO	IC max (mA)
TO-39	2N5109	NPN	200	3	10	15		12	1200	3.5	20	400
TO-39	MRF5943C	NPN	200	3.4	30	15		11.4	1000		30	400
SO-8	MRF5943, R1, R2	NPN	200	3.4	30	15		15	1300		30	400
TO-72	2N5179	NPN	200	4.5	1.5	6		17	900	1	12	50
TO-72	2N2857	NPN	300	5.5	50	6		13	1600	1	15	40
TO-39	MRF517	NPN	300	7.5	50	15		5.5	4600	3	25	150
TO-72	MRF904	NPN	450	1.5	5	6		11	4000	1	15	30
TO-72	2N6304	NPN	450	5	2	5		14	1400	1	15	50
MACRO T	BFR91	NPN	500	1.9	2	5	11	16.5	5000	1	12	35
MACRO T	BFR96	NPN	500	2	10	10		14.5	500	2.6	15	100
SO-8	MRF5812, R1, R2	NPN	500	2	50	10	15.5	17.8	5000		15	200
MACRO X	MRF581A	NPN	500	2	50	10	14	15	5000		15	200
Macro	BFR90	NPN	500	2.4	2	10	15	18	5000	1	15	30
TO-72	BFY90	NPN	500	2.5	2	5		20	1300		15	50
TO-72	MRF914	NPN	500	2.5	5	10		15	4500		12	40
MACRO X	MRF581	NPN	500	2.5	50	10	15	17.8	5000		16	200
TO-39	MRF586	NPN	500	3	90	15	11	14.5	4500	2.2	17	200
MACRO X	MRF951	NPN	1000	1.3	5	6	14	17	8000	0.45	10	100
MACRO X	MRF571	NPN	1000	1.5	10	6	10		8000	1	10	70
MACRO T	BFR91	NPN	1000	2.5	2	5	8	11	5000	1	12	35
MACRO T	BFR90	NPN	1000	3	2	10	10	12.5	5000	1	15	30
TO-39	MRF545	PNP				Ī		14	1400	2	70	400
TO-39	MRF544	NPN						13.5	1500		70	400

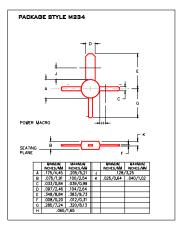
RF (Low Power PA / General Purpose) Selection Guide

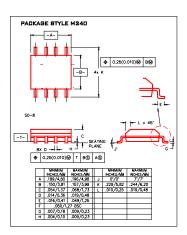
RF (LNA / General Purpose) Selection Guide

# **Low Cost RF Plastic Package Options**



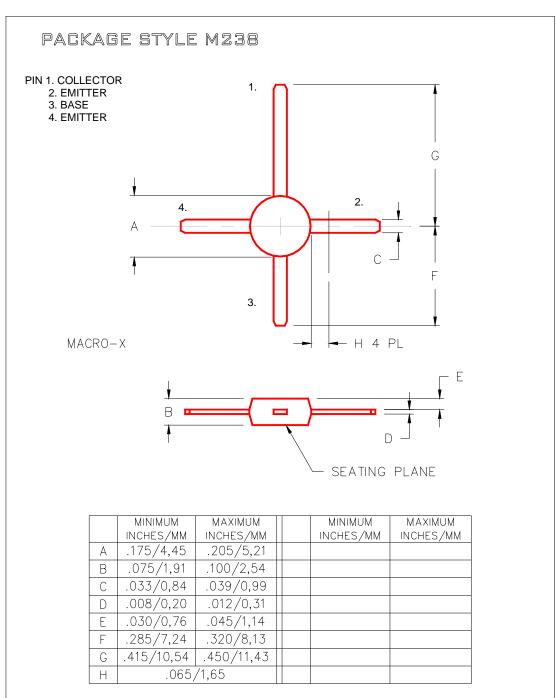






Macro T Macro X Power SO-8





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